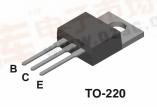
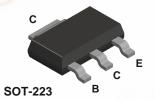


## D45C11

# NZT45C11





## **PNP Current Driver Transistor**

This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from Process 5P. See NZT751 for characteristics.

## Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	80	V
Ic	Collector Current - Continuous	4.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		D45C11	*NZT45C11	C CO
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	60 480	1.2 9.7	W mW/°C
R <sub>θ</sub> JC	Thermal Resistance, Junction to Case	2.1		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	103	°C/W

Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>. WWW.DZSC

## **PNP Current Driver**

(continued)

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
055 0114	DAOTEDIOTIOO				
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 100 \text{ mA}, I_B = 0$	60		V
I <sub>CES</sub>	Collector-Cutoff Current	V <sub>CB</sub> = 90 V, I <sub>E</sub> = 0		10	μА
Ево	Emitter-Cutoff Current	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0		100	μΑ
ON CHAP	RACTERISTICS				
	RACTERISTICS		10	100	
	RACTERISTICS  DC Current Gain	I <sub>C</sub> = 0.2 A, V <sub>CE</sub> = 1.0 V	40	120	
h <sub>FE</sub>		$I_C = 0.2 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ A}, I_B = 50 \text{ mA}$	40 20	120	V
ON CHAF  hFE  VCE(sat)  VBE(sat)	DC Current Gain	Ic = 1.0 A, V <sub>CE</sub> = 1.0 V	-		V
N <sub>FE</sub>	DC Current Gain  Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 1.0 V I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 50 mA	-	0.5	
N <sub>FE</sub> V <sub>CE(sat)</sub> V <sub>BE(sat)</sub>	DC Current Gain  Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 1.0 V I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 50 mA	-	0.5	

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